

In re Application of: Tadatomo et al.

Application No. 09/936,683

Filed: November 30, 2001

For: SEMICONDUCTOR BASE AND ITS MANUFACTURING METHOD, AND
SEMICONDUCTOR CRYSTAL MANUFACTURING METHODCOMMISSIONER FOR PATENTS
Washington, D.C. 20231

Sir:

Transmitted herewith is a Response to Office Action in the subject application.

☐ Applicants claim small entity status of this application under 37 CFR 1.27.☒ Petition For Extension Of Time☐ Applicants petition for a extension of time under 37 CFR 1.136, the fee for which is \$ (enclosed).☒ Applicants believe that no petition for an extension of time is necessary. However, to the extent that such petition is deemed necessary, Applicants hereby petition for a sufficient extension of time to render the present submission timely. Please charge Deposit Account No. 12-1216 for the appropriate petition fee.☒ No additional claim fee is required.☒ Other: Patent Abstract of Japan corresponding to JP 10-178026

The claim fee has been calculated as shown below:

					SMALL ENTITY		OTHER THAN A SMALL ENTITY	
	CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR	EXTRA CLAIMS PRESENT	RATE	ADDIT. CLAIM FEE	RATE	ADDIT. CLAIM FEE
TOTAL	20	MINUS	21	=0	x 9=	\$	x 18=	\$0.00
INDEPENDENT	5	MINUS	5	=0	x 40=	\$	x 80=	\$0.00
<input type="checkbox"/>	FIRST PRESENTATION OF MULTIPLE CLAIM				+ 135=	\$	+ 270=	\$0.00
					TOTAL	\$	TOTAL	\$0.00

☐ Please charge my Deposit Account No. 12-1216 in the amount of \$. A duplicate copy of this sheet is attached.☐ A check in the amount of \$ is attached.☒ The Commissioner is hereby authorized to charge any deficiencies in the following fees associated with this communication or credit any overpayment to Deposit Account No. 12-1216. A duplicate copy of this sheet is attached.☒ Any filing fees under 37 CFR 1.16 for the presentation of extra claims.☒ Any patent application processing fees under 37 CFR 1.17.

Respectfully submitted,

LEYDIG, VOIT & MAYER, LTD.

By

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PATENT
Attorney Docket No. 213578
Client Reference No. 20836

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Tadatomo et al.

Application No. 09/936,683

Art Unit: 2826

Examiner: F. Erdem

Filed: November 30, 2001

For: SEMICONDUCTOR BASE AND ITS
MANUFACTURING METHOD, AND
SEMICONDUCTOR CRYSTAL
MANUFACTURING METHOD

RESPONSE TO OFFICE ACTION

Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

In response to the Office Action dated November 20, 2002, please enter the following amendments and consider the following remarks.

AMENDMENTS

IN THE CLAIMS:

Please replace claim 1 with the following:

1. A semiconductor base comprising a substrate and a semiconductor crystal formed on said substrate by vapor phase growth, wherein (a) the semiconductor crystal is a GaN group semiconductor crystal defined by $Al_x Ga_{1-x-y} In_y N$ where $0 \leq x \leq 1$ and $0 \leq y \leq 1$, (b) the substrate has a concavo-convex surface as a crystal growth plane, and (c) the semiconductor crystal is grown exclusively from an upper part of a convex part of the concavo-convex surface.

Please cancel claim 2.

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